



# STD60NF55L

N-CHANNEL 55V - 0.012Ω - 60A DPAK  
STripFET™ II POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD60NF55L	55V	< 0.015Ω	60A

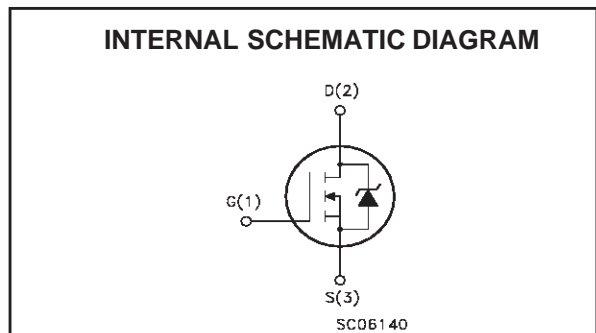
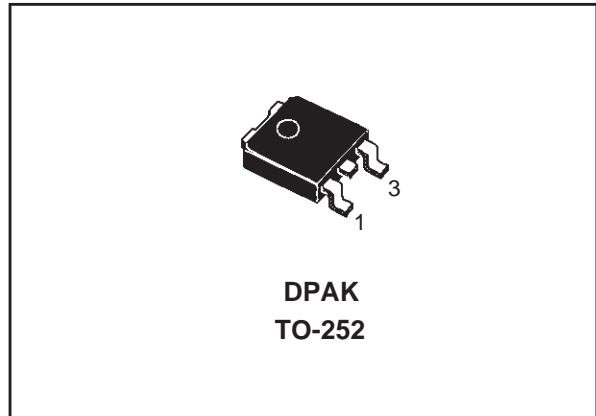
- TYPICAL R<sub>DS(on)</sub> = 0.012Ω
- LOW THRESHOLD DRIVE
- ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL

## DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

## APPLICATIONS

- AUTOMOTIVE
- MOTOR CONTROL



## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	55	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	55	V
V <sub>GS</sub>	Gate- source Voltage	± 15	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	60	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	42	A
I <sub>DM</sub> (1)	Drain Current (pulsed)	240	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	110	W
	Derating Factor	0.73	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	16	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	400	mJ
T <sub>stg</sub>	Storage Temperature	- 55 to 175	°C
T <sub>j</sub>	Operating Junction Temperature		

(●) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 40A, di/dt ≤ 350A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(2) Starting T<sub>j</sub>=25°C, I<sub>D</sub>=30A, V<sub>DD</sub>=20V

## STD60NF55L

### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.36	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose	275	°C

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	55			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 15 V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1		2	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A V <sub>GS</sub> = 5 V, I <sub>D</sub> = 30 A		0.012 0.014	0.015 0.017	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 30 A		35		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		1950		pF
C <sub>oss</sub>	Output Capacitance			390		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			130		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 25\text{ V}, I_D = 30\text{ A}$		30		ns
$t_r$	Rise Time	$R_G = 4.7\Omega, V_{GS} = 4.5\text{ V}$ (see test circuit, Figure 3)		180		ns
$Q_g$	Total Gate Charge	$V_{DD} = 40\text{ V}, I_D = 60\text{ A},$		40		nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 5\text{ V}$		10		nC
$Q_{gd}$	Gate-Drain Charge			20		nC

**SWITCHING OFF**

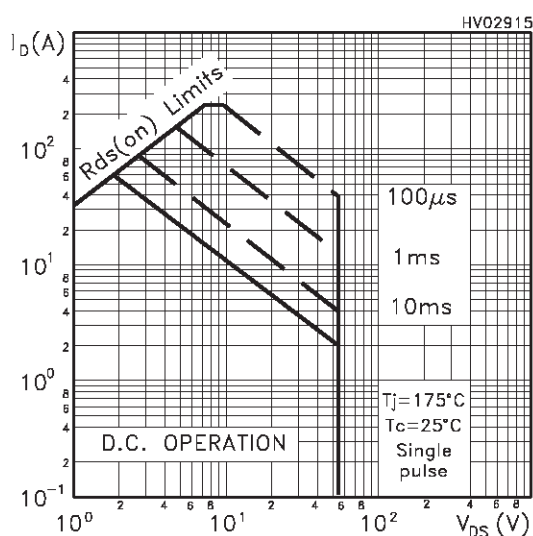
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 25\text{ V}, I_D = 30\text{ A},$		80		ns
$t_f$	Fall Time	$R_G = 4.7\Omega, V_{GS} = 4.5\text{ V}$ (see test circuit, Figure 3)		35		ns

**SOURCE DRAIN DIODE**

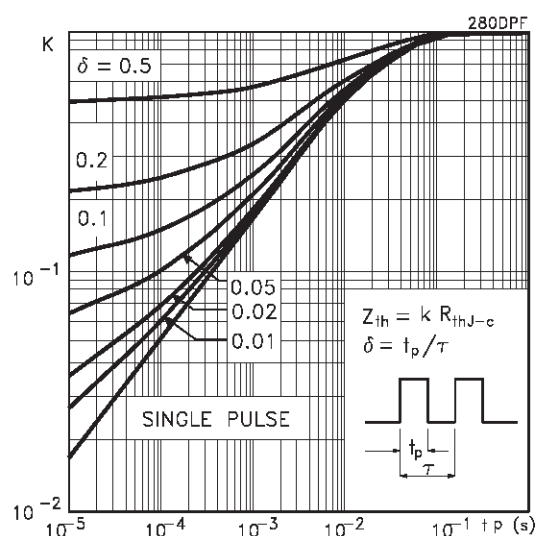
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				60	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				240	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 60\text{ A}, V_{GS} = 0$			1.3	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 40\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$		65		ns
$Q_{rr}$	Reverse Recovery Charge	$V_{DD} = 25\text{ V}, T_j = 150\text{ }^\circ\text{C}$		130		nC
$I_{RRM}$	Reverse Recovery Current	(see test circuit, Figure 5)		4		A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

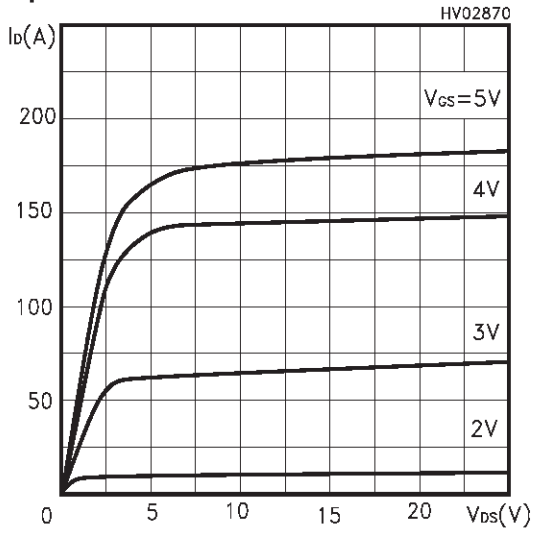
**Safe Operating Area**



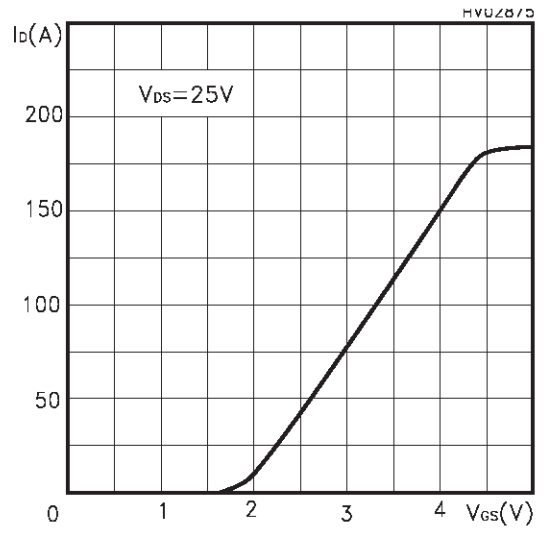
**Thermal Impedance**



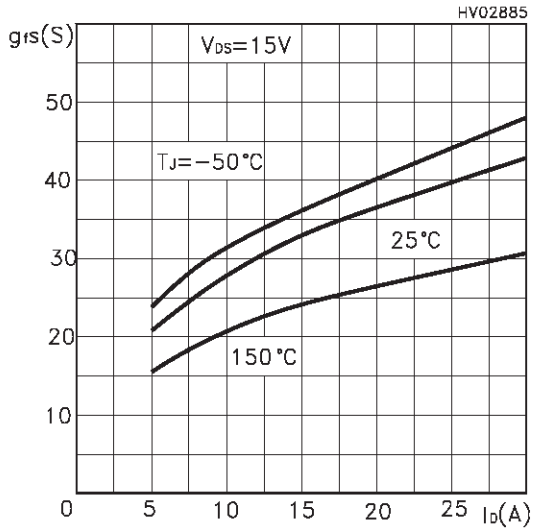
Output Characteristics



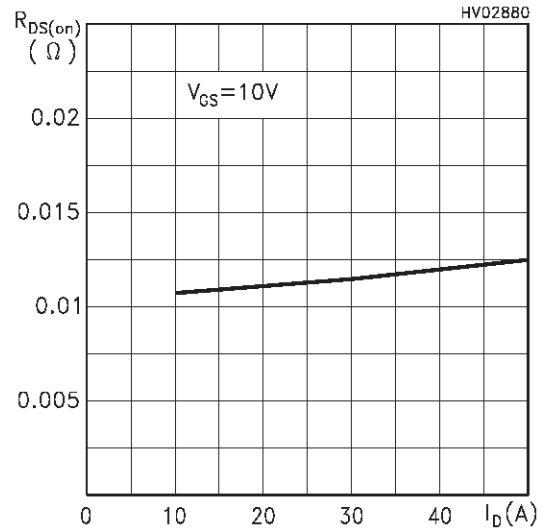
Transfer Characteristics



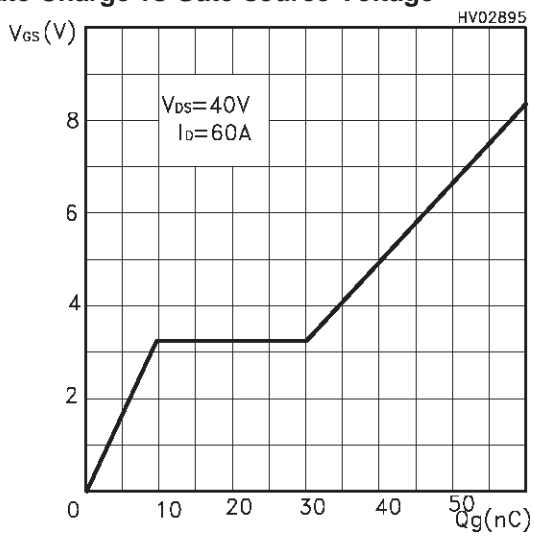
Transconductance



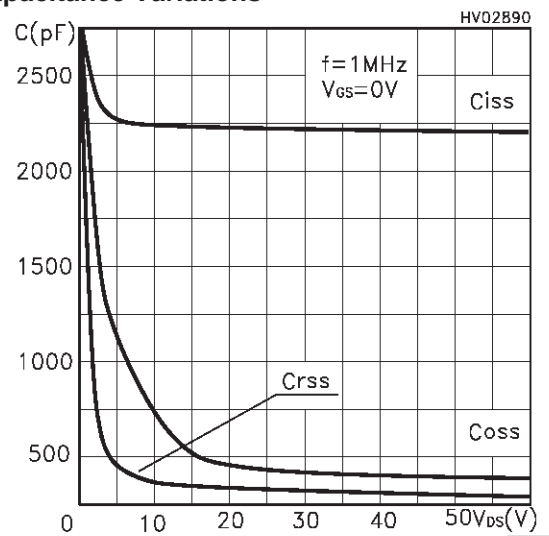
Static Drain-source On Resistance



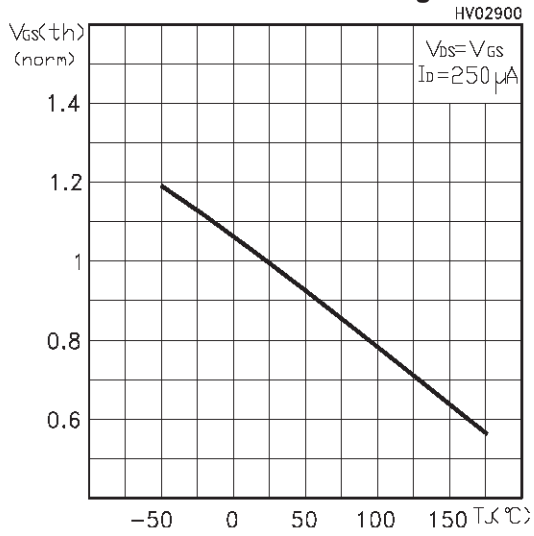
Gate Charge vs Gate-source Voltage



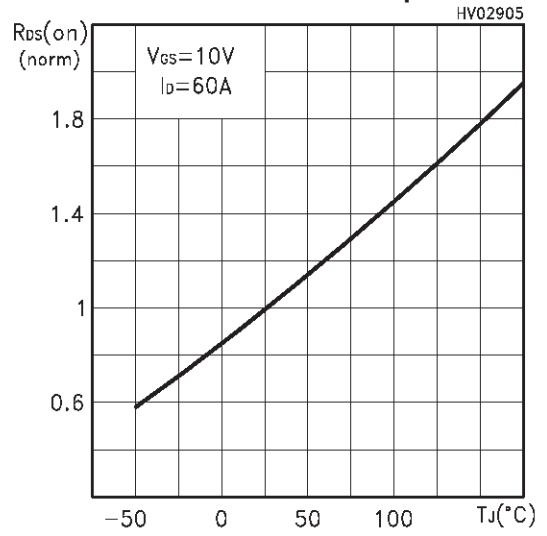
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

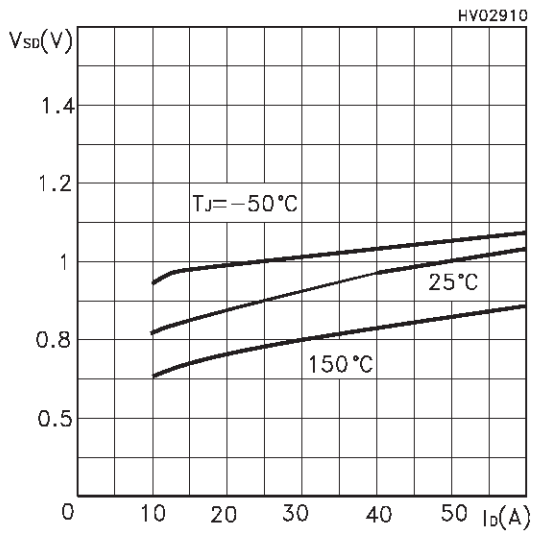


Fig. 1: Unclamped Inductive Load Test Circuit

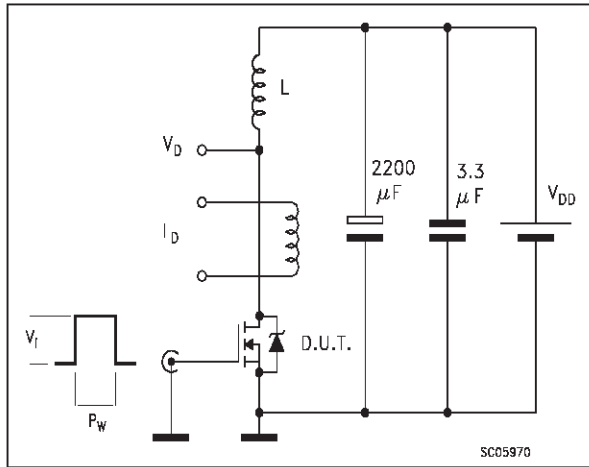


Fig. 2: Unclamped Inductive Waveform

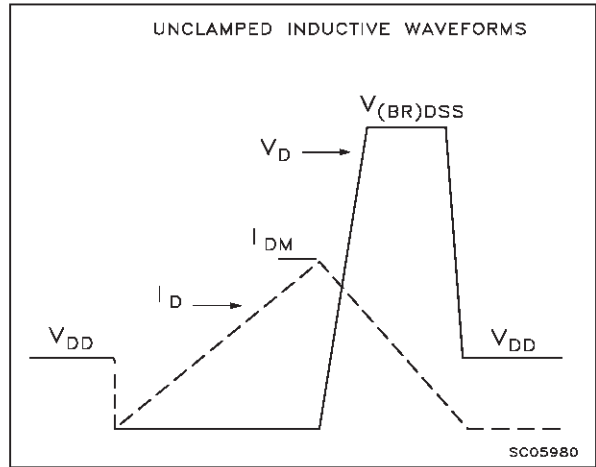


Fig. 3: Switching Times Test Circuit For Resistive Load

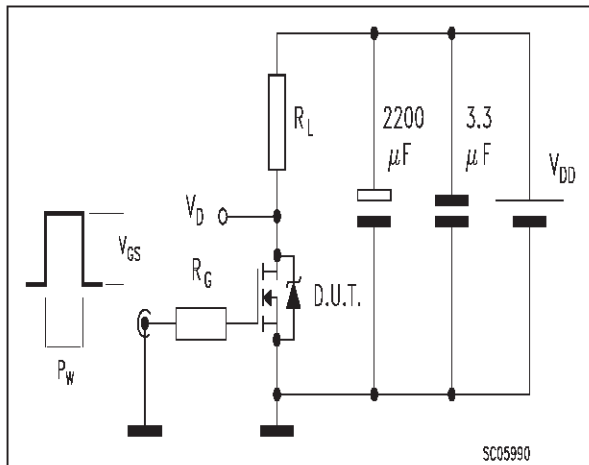


Fig. 4: Gate Charge test Circuit

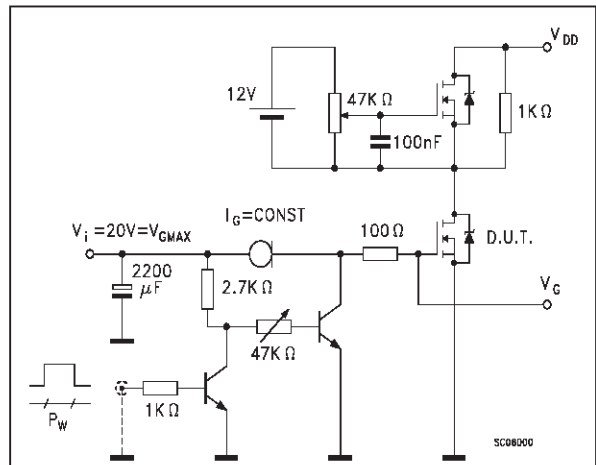
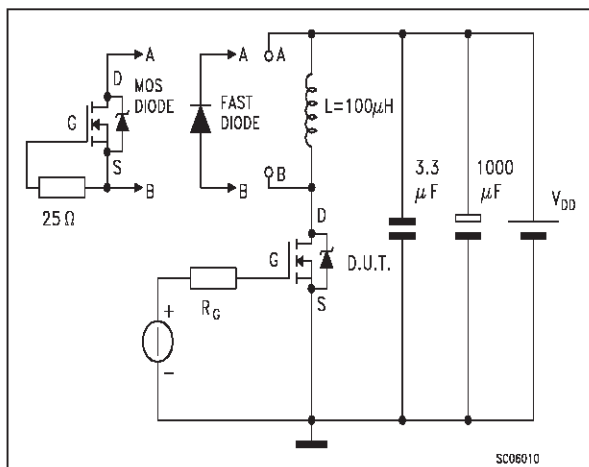
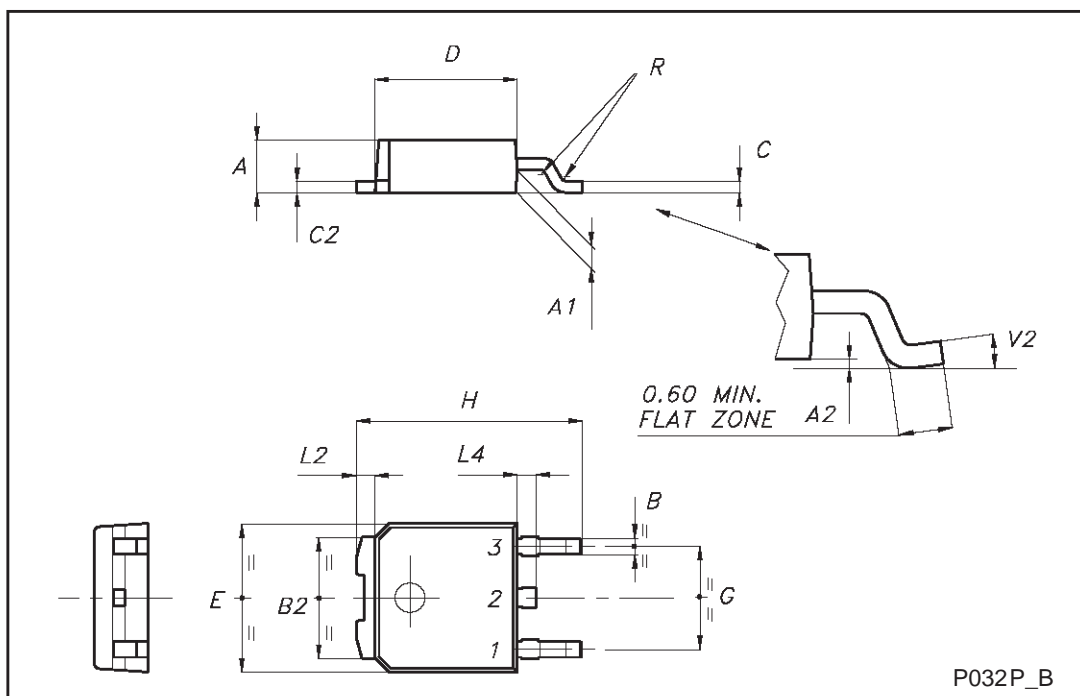


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

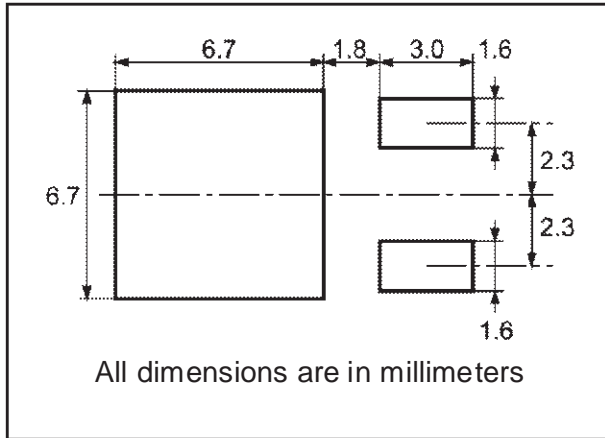


TO-252 (DPAK) MECHANICAL DATA

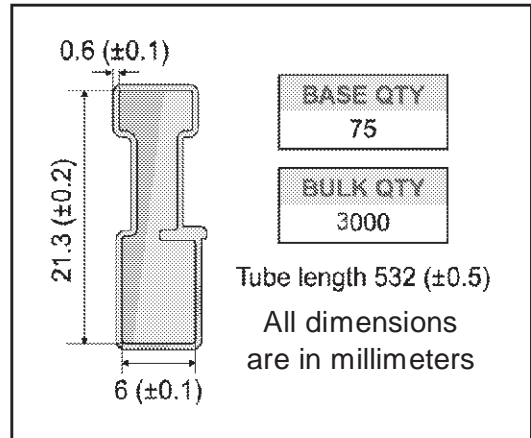
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



**DPAK FOOTPRINT**



**TUBE SHIPMENT (no suffix)\***



**TAPE AND REEL SHIPMENT (suffix "T4")\***

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

TOP COVER TAPE

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

10 pitches cumulative tolerance on tape +/- 0.2 mm

For machine ref. only including draft and radii concentric around B0

\*on sales type



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